

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	0	257/68,71,295-314,324-326.ccls	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/07 11:48
S2	10279	257/68,71,295-314,324-326.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/23 15:02
S3	2051	438/3,240.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/23 15:03
S4	11924	257/68,71,295-314,324-326.ccls. or 438/3,240.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/23 15:03
S5	1	(257/68,71,295-314,324-326.ccls. or 438/3,240.ccls.) and (((plate adj line\$1) PL) near5 extend\$3 near5 adjacent near5 (ferroelectric adj capacitor\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/23 15:09
S6	74	(257/68,71,295-314,324-326.ccls. or 438/3,240.ccls.) and (((plate adj line\$1) PL) near5 (ferroelectric adj capacitor\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/23 15:33
S7	1	"6600185".PN.	USPAT	OR	ON	2004/09/23 15:27
S8	120	(257/68,71,295-314,324-326.ccls. or 438/3,240.ccls.) and (((plate adj line\$1) PL) with (ferroelectric adj capacitor\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/23 15:46
S10	624	("257"/\$.ccls. "438"/\$.ccls. "365"/\$.ccls.) and (((plate adj line\$1) PL) with (ferroelectric adj capacitor\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/23 16:07
S11	20	((("257"/\$.ccls. "438"/\$.ccls. "365"/\$.ccls.) and (((plate adj line\$1) PL) with (ferroelectric adj capacitor\$1))) and ((interlayer near dielectric) ILD)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/23 16:07
S12	790	((plate adj line\$1) PL) with (ferroelectric adj capacitor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 11:34

S13	21	((plate adj line\$1) PL) with (ferroelectric adj capacitor\$1)) and ((interlayer near dielectric) ILD)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/23 16:08
S14	15	((plate adj line\$1) PL) with (ferroelectric adj capacitor\$1)) and substrate) and (hydrogen near barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/04 16:56
S15	280	((plate adj line\$1) PL) with (ferroelectric adj capacitor\$1)) and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/23 16:15
S16	147	(ferroelectric near capacitor\$1) with ((interlayer near dielectric) ILD)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/04 16:58
S17	407	(ferroelectric near capacitor\$1) with ((interlayer near (insulat\$3 dielectric)) ILD)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/04 16:59
S18	183	S17 and plate	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/01/04 16:59
S19	425234	"257"/\$.ccls. "438"/\$.ccls. "365"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/04 09:10
S20	436	S19 and ((lower bottom upper top) near electrode) near2 (ruthenium Ru RuO2 (ruthenium adj oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/04 09:12
S21	83	S20 and (ferroelectric adj capacitor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 11:32
S22	68	S21 and (PZT(Pb, Zr, TiO3) near PbTiO3)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 11:31

S23	0	S21 and (PbTiO3 near2 seed)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/04 09:43
S24	117	((plate adj line\$1) PL) near (ferroelectric adj capacitor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/05 16:27
S25	0	((plate adj line\$1) PL) near (two near adjacent near ferroelectric adj capacitor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/05 16:26
S26	0	((plate adj line\$1) PL) near (two near adjacent near ferroelectric near capacitor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/05 16:27
S27	4	("5959879"   "6004839"   "6310374"   "6410397").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/05 16:49
S28	14	("4888630"   "5300799"   "5412596"   "5515311"   "5517445"   "5523964"   "5541871"   "5559733"   "5623439"   "5753946"   "5768185"   "5822239"   "5822240"   "5856688").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/05 16:52
S29	11770	ferroelectric near (capacitor\$1 film\$1 layer\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/07 11:49
S30	6	S29 and (hydrogen near barrier near (sidewall\$1 (side near wall\$1) spacer\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/07 12:53
S31	5	("6011284"   "6144060"   "6201726"   "6242299"   "6396092").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/07 11:58
S32	275	S29 and (hydrogen near barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/07 12:53
S33	81	S32 and (PL (plate near line\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/07 15:33
S34	4	("5959879"   "6004839"   "6310374"   "6410397").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/07 13:02

S35	11770	ferroelectric near (capacitor\$1 film\$1 layer\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/07 15:45
S36	275	S35 and (hydrogen near barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/07 18:08
S37	11	S36 and ((PL (plate near line\$1)) with (platinum ruthenium iridium rhodium Osmium))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/07 16:03
S38	2	("5959879").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/02/07 15:55
S39	60	S35 and ((PL (plate near line\$1)) with (platinum ruthenium iridium rhodium Osmium))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/07 18:01
S40	2	("6521929").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/02/07 18:01
S41	11770	ferroelectric near (capacitor\$1 film\$1 layer\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/07 18:08
S42	891	S41 and (ruthenium (ruthenium near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/07 18:09
S43	38	S41 and (electrode near (ruthenium (ruthenium near oxide)))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/07 18:30
S44	28	S41 and (((upper top lower bottom) near electrode) near (ruthenium (ruthenium near oxide)))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/07 18:31

S45	15797	(PZT(Pb, Zr, TiO3) near PbTiO3 near seed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 11:33
S46	1805	S45 and (ferroelectric adj capacitor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 11:33
S47	15797	(PZT(Pb, Zr, TiO3) near PbTiO3 near seed near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 11:37
S48	1805	S47 and (ferroelectric adj capacitor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 11:33
S49	257	S47 and (((plate adj line\$1) PL) with (ferroelectric adj capacitor\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 11:34
S50	0	PbTiO3 near seed near (layer film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 11:35
S51	0	PbTiO near seed near (layer film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 11:35
S52	0	(PZT near PbTiO near seed near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 11:37
S53	10	(PZT near seed near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 15:32

S54	20	(successive\$2 near pattern\$3 near electrode\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 15:44
S55	0	(successive\$2 near pattern\$3 near electrode\$1) with (anisotropical\$2 near etch\$3 near plasma near oxygen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 15:34
S56	0	electrode\$1 with (anisotropical\$2 near etch\$3 near plasma near oxygen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 15:35
S57	2	(anisotropical\$2 near etch\$3 near plasma near oxygen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 15:43
S58	778	(anisotropical\$2 near etch\$3) and (plasma near oxygen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 15:43
S59	40	S58 and (pattern\$3 near electrode\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 16:42
S60	0	(ferroelectric near (layer film)) near2 (chemical near solution near deposition) near2 precursor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 16:44
S61	0	(ferroelectric near (layer film)) with (chemical near solution near deposition) near2 precursor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 16:44
S62	0	(ferroelectric near (layer film)) near2 (chemical near solution near deposition) near2 precursor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/08 16:44

S63	1	(ferroelectric near (layer film)) with (chemical near solution near deposition) near2 precursor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/09 08:44
S64	24	(ferroelectric near (layer film)) with (chemical near solution near deposition)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/09 08:53
S65	3	((chemical near solution near deposition) CSD) near2 precursor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/09 08:50
S66	1160	precursor near ((lead near acetate) Pb zirconium Zr (titanium near isopropoxide) Ti)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/09 08:52
S67	101	S66 and (ferroelectric near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/09 08:53
S68	0	S67 and (solvent near methoxyethano)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/09 08:54
S69	75	S67 and (solvent methoxyethano)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/09 08:54